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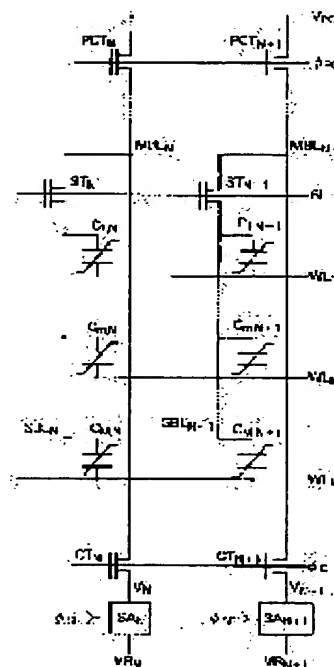
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## (54) FERROELECTRIC STORAGE DEVICE AND ITS MANUFACTURE

## (57)Abstract:

**PROBLEM TO BE SOLVED:** To realize a large-capacity ferroelectric storage device wherein many memory cells can be integrated each of which comprises only one ferroelectric capacitor.

**SOLUTION:** Respective main bit lines MBLN, MBLN+1 laid in the form of columns are connected selectively with arbitrary auxiliary bit lines SBLN, SBLN+1 from among a plurality of auxiliary bit lines via selection transistors STN, STN+1. In the grid positions wherein a plurality of word lines WL1-WLM laid in the form of rows intersect the foregoing auxiliary bit lines, memory cells Cm,N, Cm,N+1 comprising ferroelectric capacitors are disposed one by one. Further, one electrode of each foregoing ferroelectric capacitor is connected with each foregoing auxiliary bit line, and the other electrode of each foregoing ferroelectric capacitor is connected with each foregoing word line.



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